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Nanoscale heterogeneities at Transition Metal Dichalcogenide-Au Interfaces

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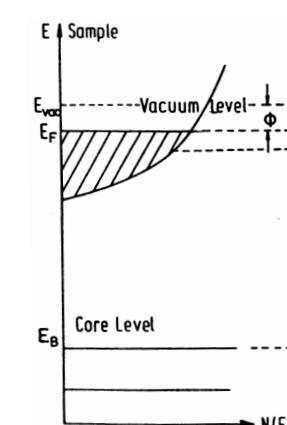
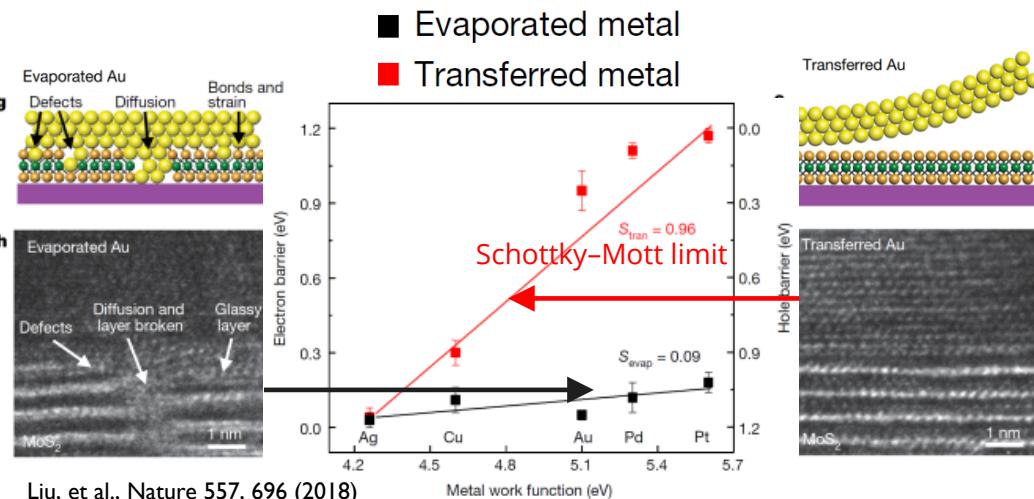
TMD-metal contact impacts device performance



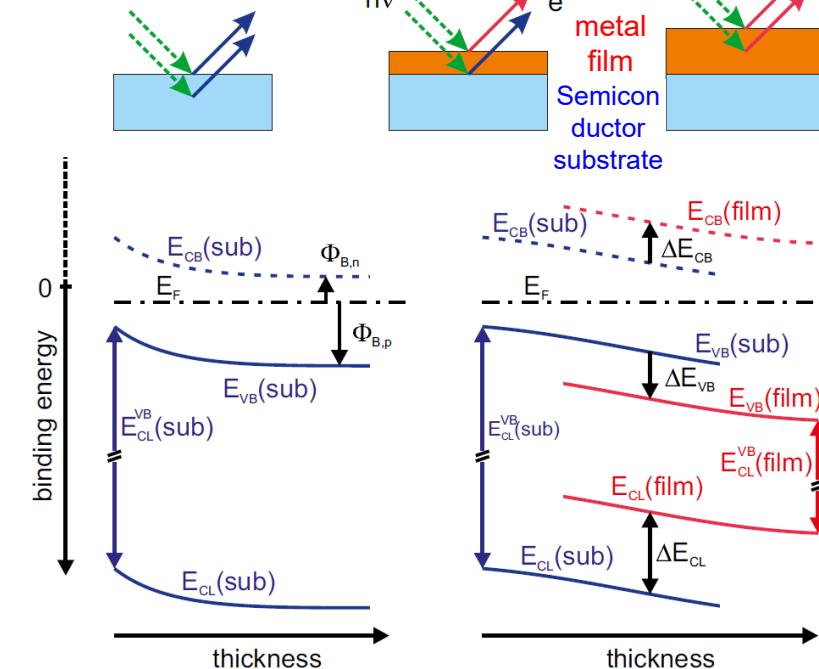
- **Transition metal dichalcogenides (TMD) is a new class of semiconductors** with enormous technological implications
- **TMD-metal contact is a critical component** to incorporate 2D materials in electronic devices

Questions:

- What are the difference of the TMD-metal interfaces fabricated via evaporation vs transfer?
- Are there heterogeneities in the electronic structure at the TMD-metal interfaces?
 - Impacts of the microstructures of Au or TMD?



Hufner, Photoelectron Spectroscopy (1995)



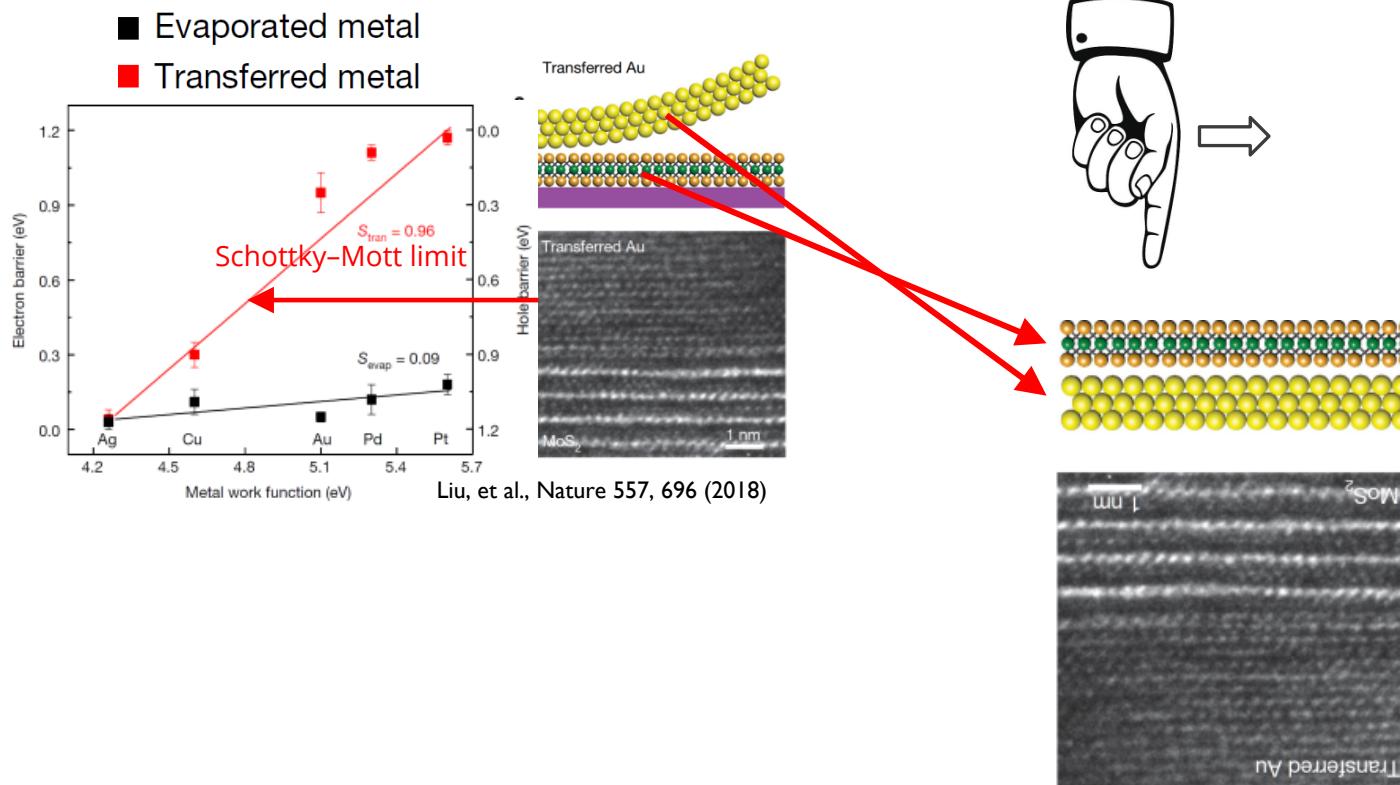
Klein, J. Am. Ceram. Soc., 99 [2] 369–387 (2016)

Challenges in examining TMD-metal contact using photoelectron spectroscopy:

- Object of interest is buried preventing direct access to the valence states
 - Energetics of valence states are inferred from the core level assuming $E_{CL}^{VB}(\text{sub})$ and $E_{CL}^{VB}(\text{film})$ stay unchanged
 - $E_{CL}^{VB}(\text{sub})$, $E_{CL}^{VB}(\text{film})$, & bandgap may not be constant since TMDs are susceptible to screening environment

- How about upside-down geometry?

Upside-down geometry enables access to the electronic structure of the TMD & interfaces

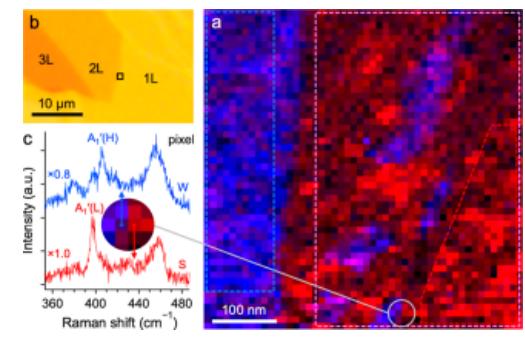
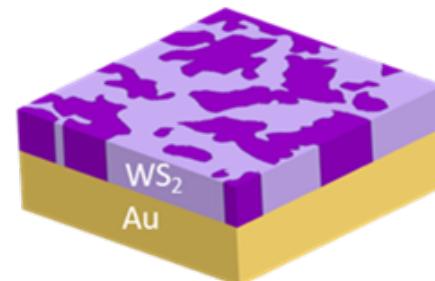


Upside-down geometry enables access to:

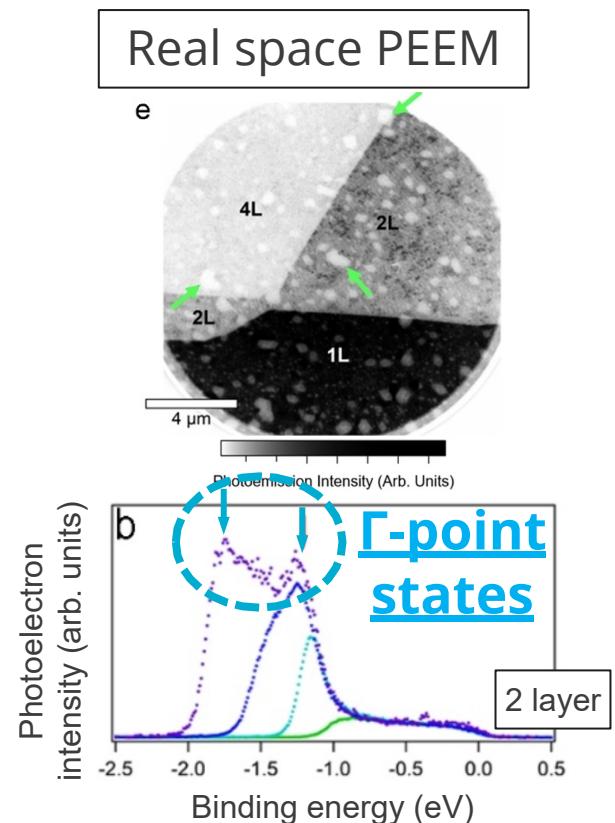
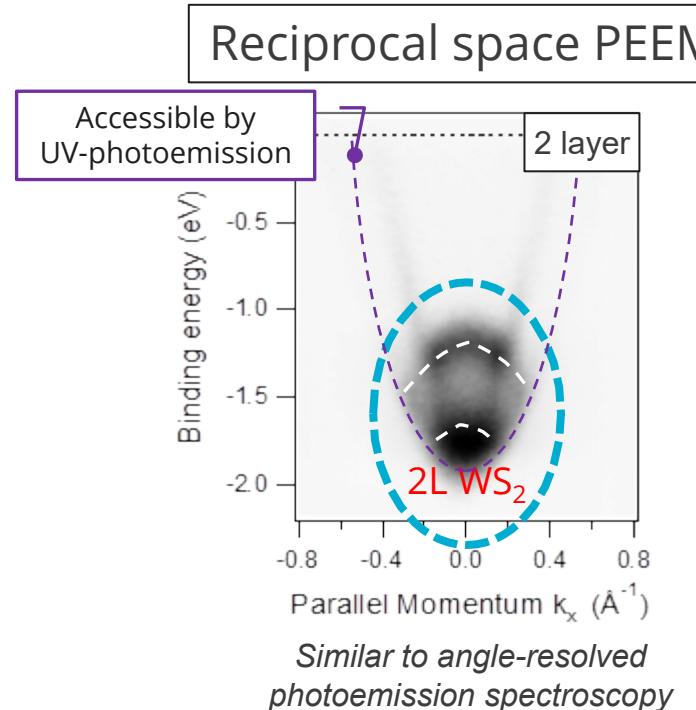
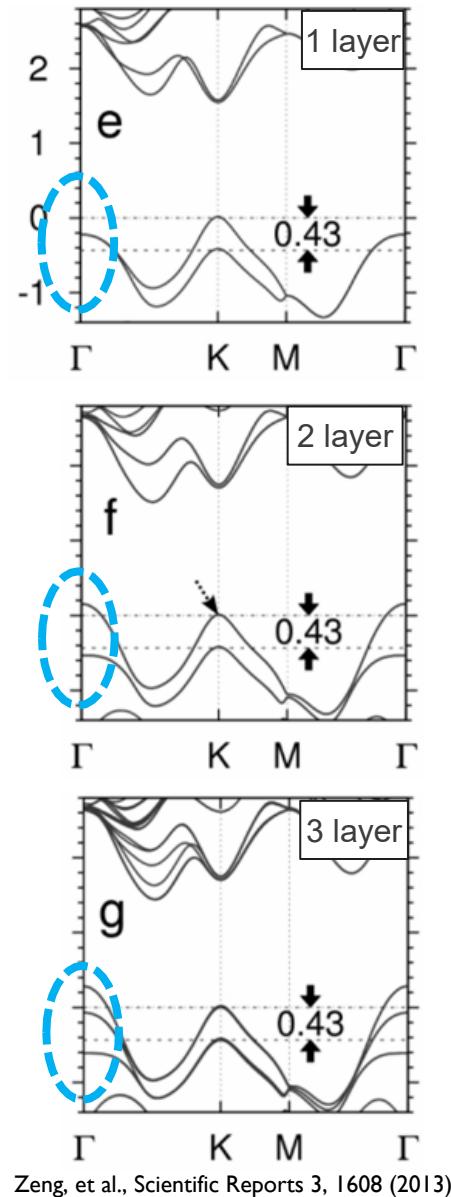
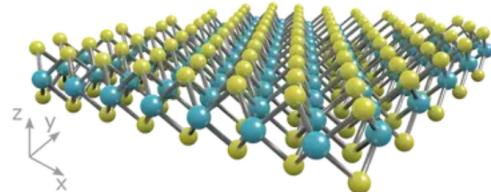
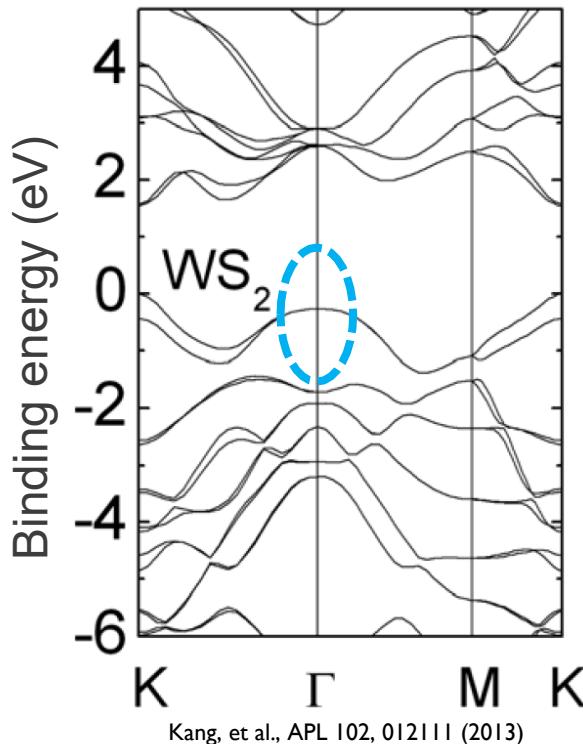
- valence band density of states in TMD
- electronic structure of a metal film (when TMD is thin)
- atomic arrangement & microstructures of TMD & metal grains

System 1: WS₂ exfoliated on a freshly deposited polycrystalline Au film

- A similar system (MoS₂ on Au) shows local variations of the surface potential, conductance, & Raman response
- Direct probe the electronic structures is desirable

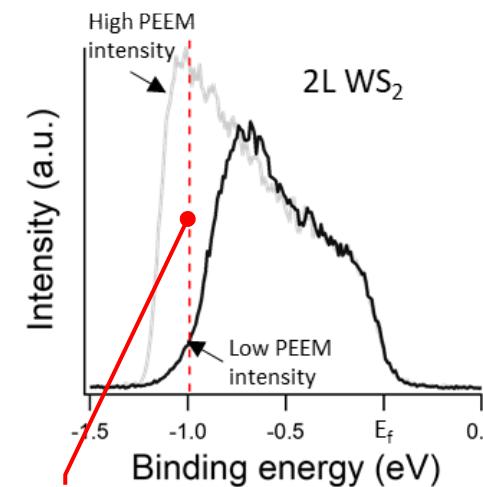
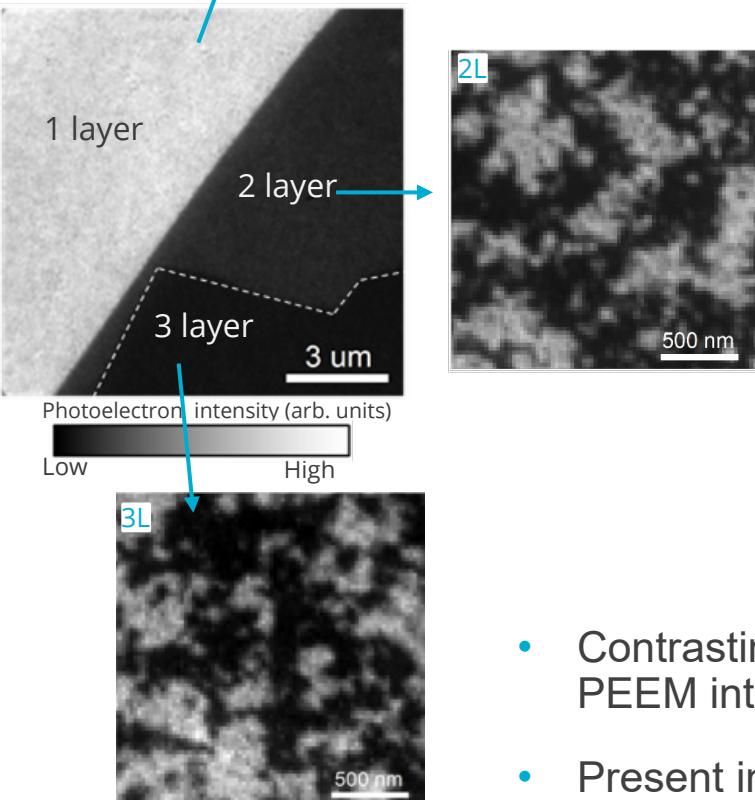
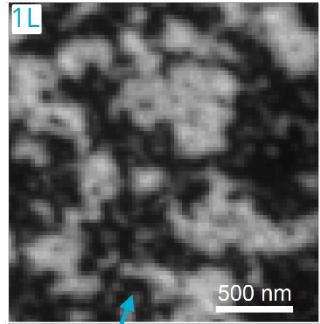


Photoelectron spectra reflect the electron dispersion of the sample



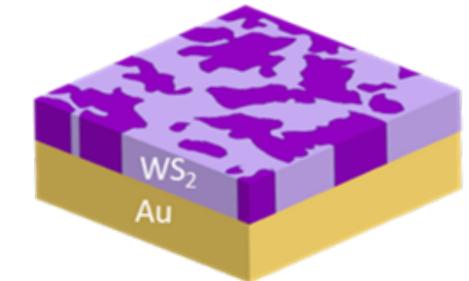
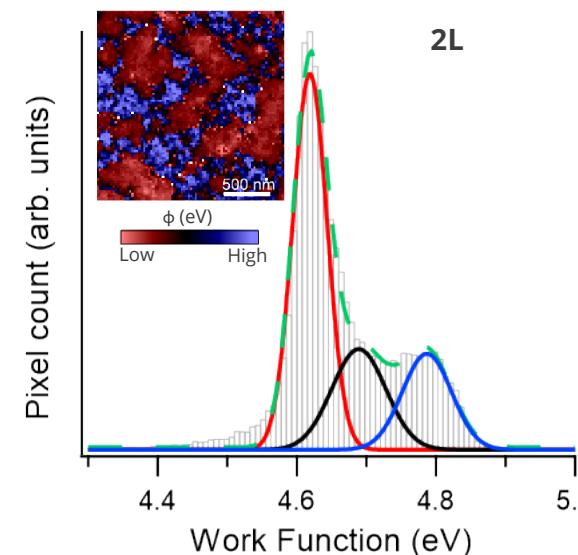
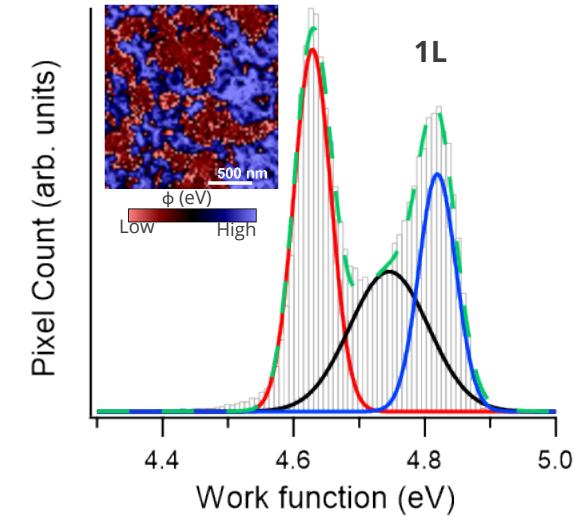
- PEEM probes the occupied electronic states in real space & reciprocal space
- Deep UV-photoemission probes the states only near the Brillouin zone center (i.e., Γ -point)

We observe submicron-scale work function heterogeneity in WS_2 exfoliated on freshly-deposited Au



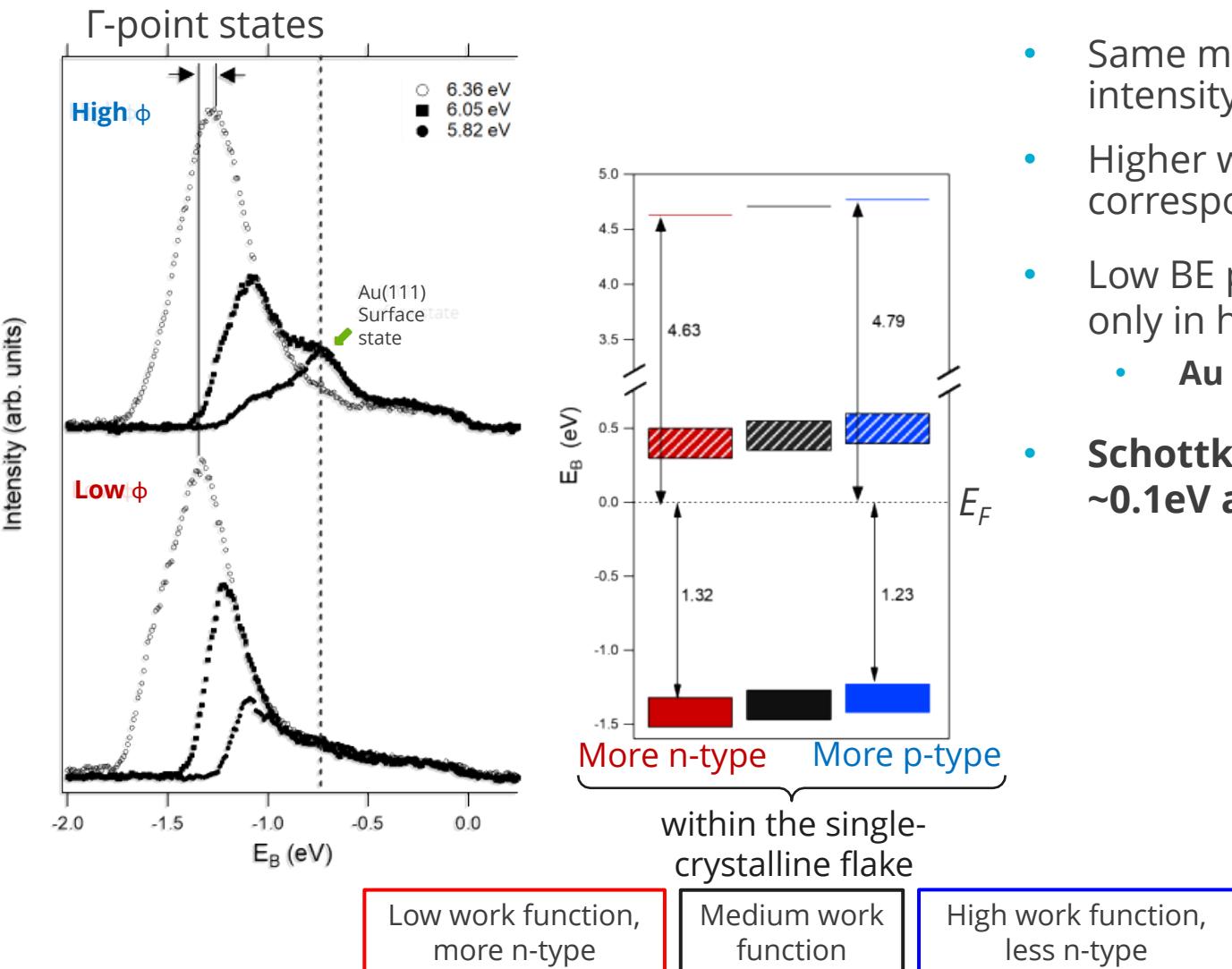
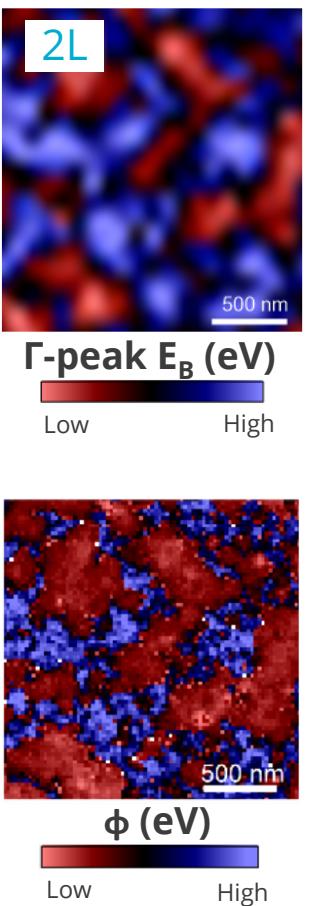
PEEM contrasts arise from difference in work function

- Contrasting μ m sized domains in PEEM intensity
- Present in 1-3L WS_2 thickness



- Large work function variation (>200 meV)
- Varying carrier density within the WS_2 flake

We determine submicron-scale carrier density variations in freshly-deposited Au-WS₂ interfaces

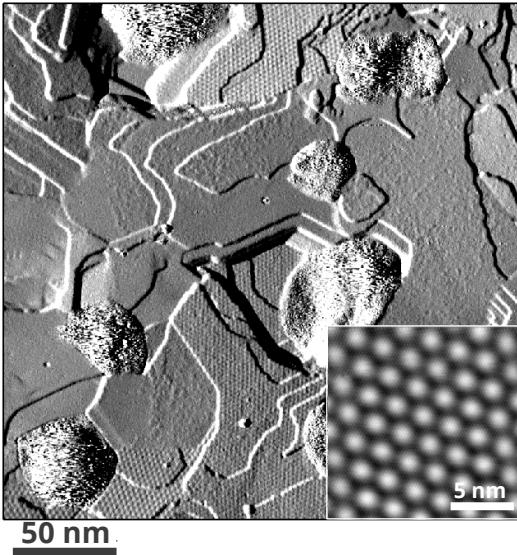


- Same micron-sized domains from photoelectron intensity & work function (ϕ) maps
- Higher work function regions show corresponding upshift in VBM
- Low BE peak (-0.7eV) observed near fermi level only in high work function areas
 - **Au (111) surface state:** impact of substrate?
- **Schottky barrier height appears to vary by ~0.1eV across the metal contact**

Three predominant crystallographic orientations of the Au grains elucidated via EBSD

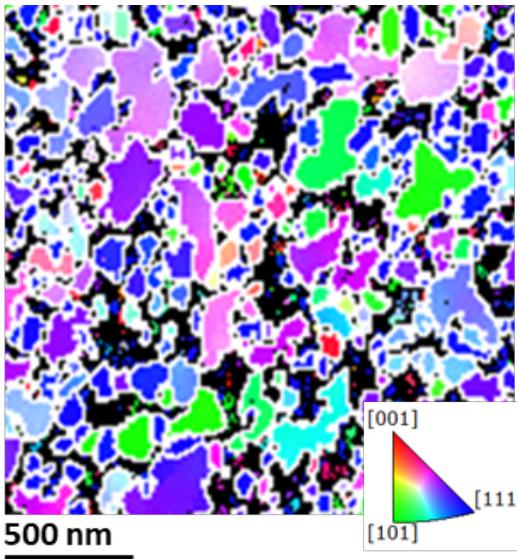


WS₂ covered as-deposited Au



Scanning tunneling microscopy:

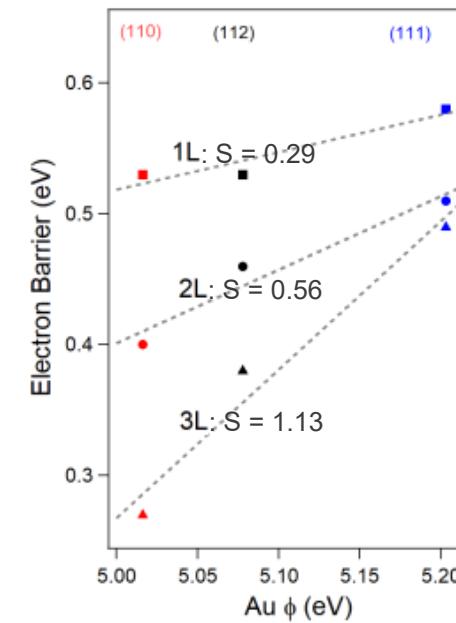
- Atomic terraces of Au & trapped blisters
- Hexagonal Moiré patterns indicate closely adhered WS₂ to Au & van der Waals interface



EBSD: Electron Backscatter Diffraction

- Majority of Au grains have (111), (112), or (110) facets according to inverse pole figure
- Consistent with localization of Moiré patterns in STM and Au(111) surface state in PEEM
- Same length scale as heterogenous electronic structure domains

Au	(110)	(112)	(111)	$\Delta\phi_{\text{Au}}$ (eV)
Φ_{Au} (eV)	5.02	5.08	5.2	0.18
WS ₂	1L	2L	3L	
$\Delta\phi_{\text{WS}_2}$ (eV)	0.18	0.16	0.13	

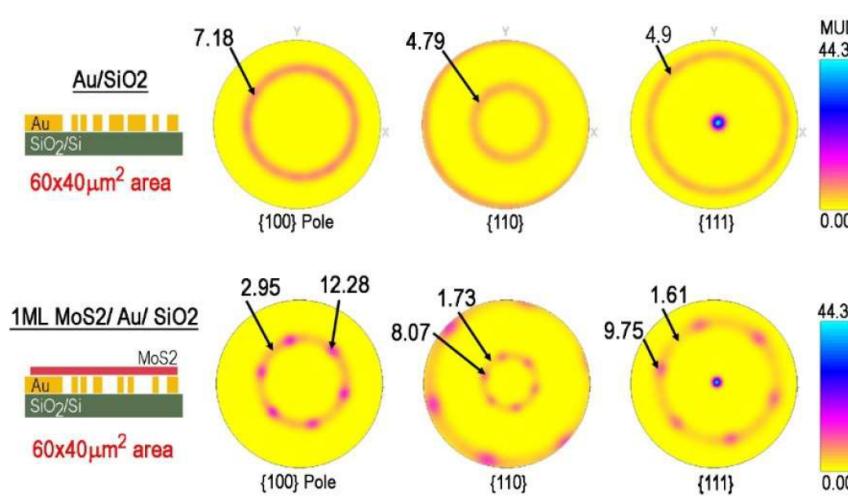
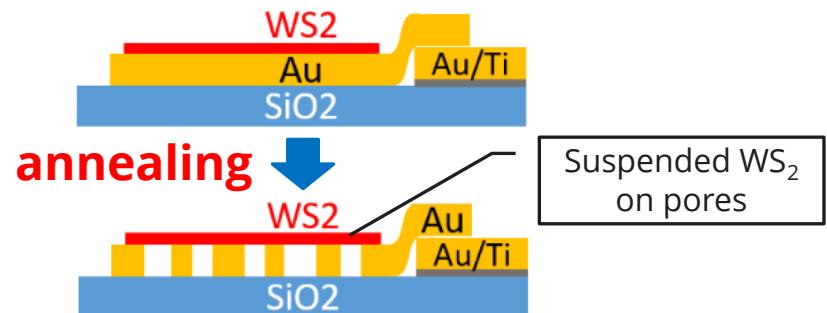


Take-home messages:

- **3 different Schottky barriers** within a single junction
- **Crystal facets of Au grains** govern the **Schottky barrier height** between Au & WS₂
- Relatively high S (pinning factor or interface parameter) expected for van der Waals bonding

What happens if there are WS_2 -Au(111) interfaces only?

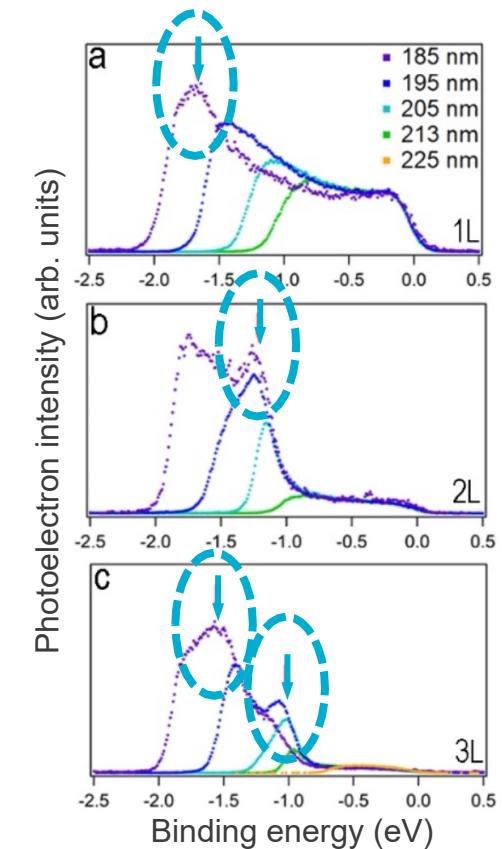
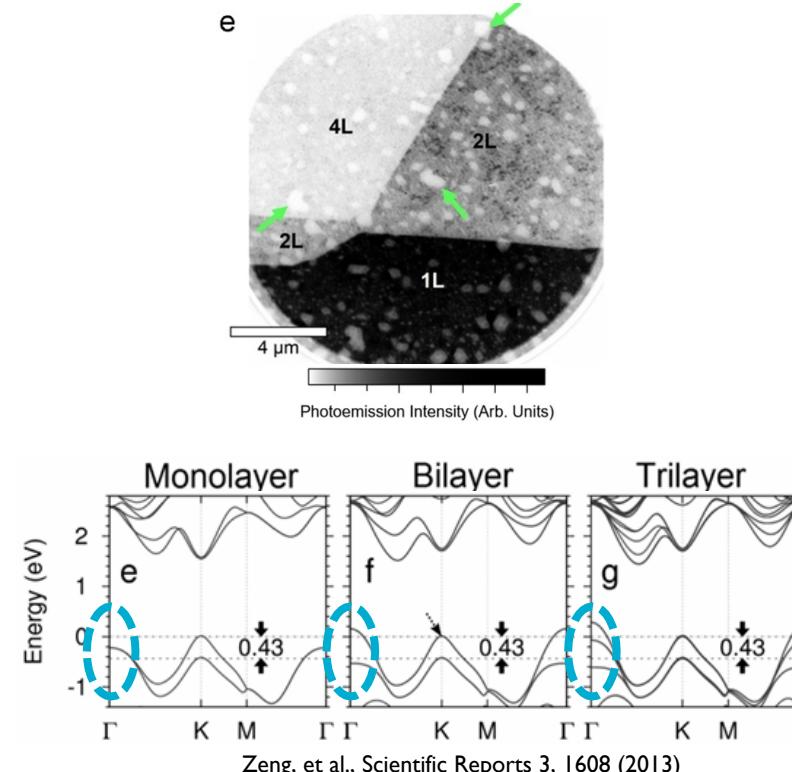
- System 2: Reflow & recrystallization create WS_2 -Au(111) interface with pseudo-epitaxial relation



EBSD confirmed pseudo-epitaxial interface

Fonseca, et al., Nature Communications 11, 5 (2020)

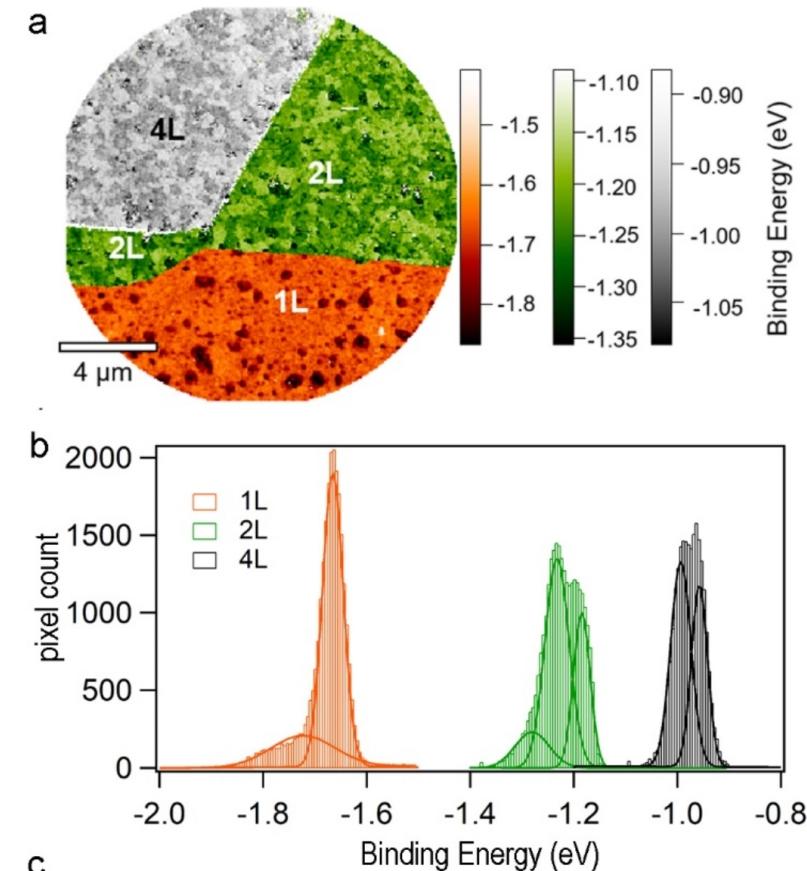
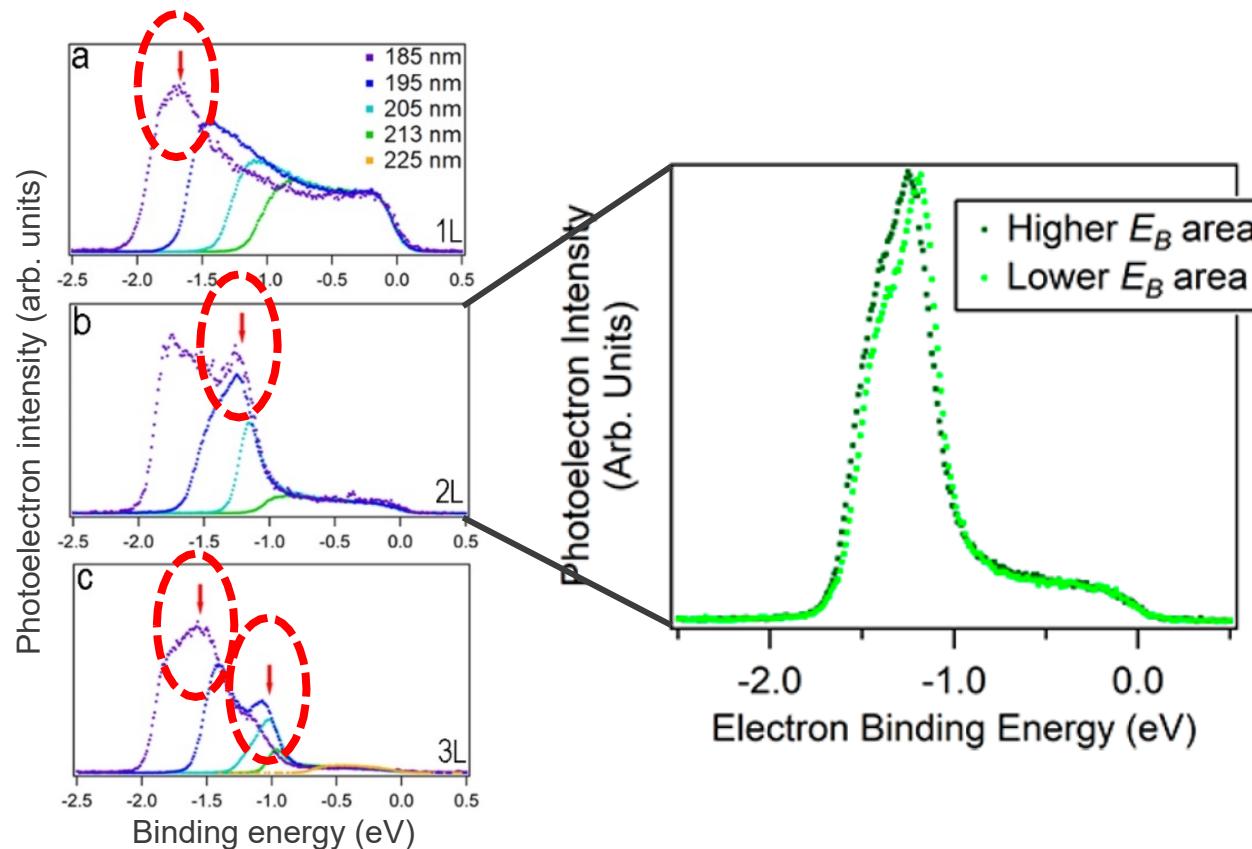
- Photoelectron spectra show characteristic splitting of the highest occupied states at Γ -point in this pseudo-epitaxial WS_2 -Au system



Zeng, et al., Scientific Reports 3, 1608 (2013)

Thomas, et al., ACS Nano, 15, 18060, 2021

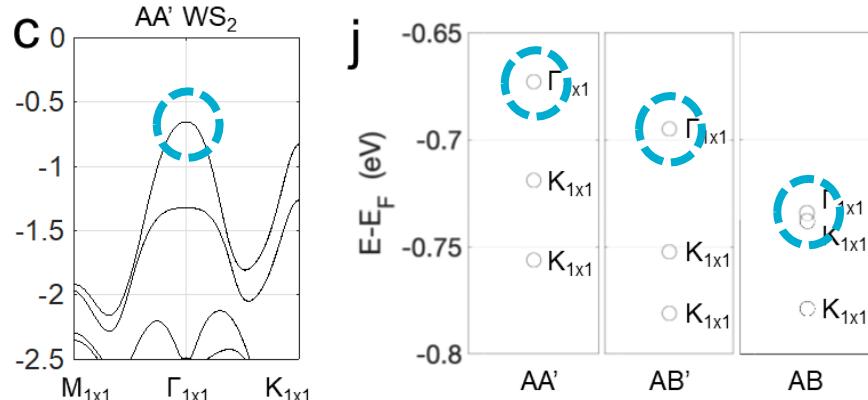
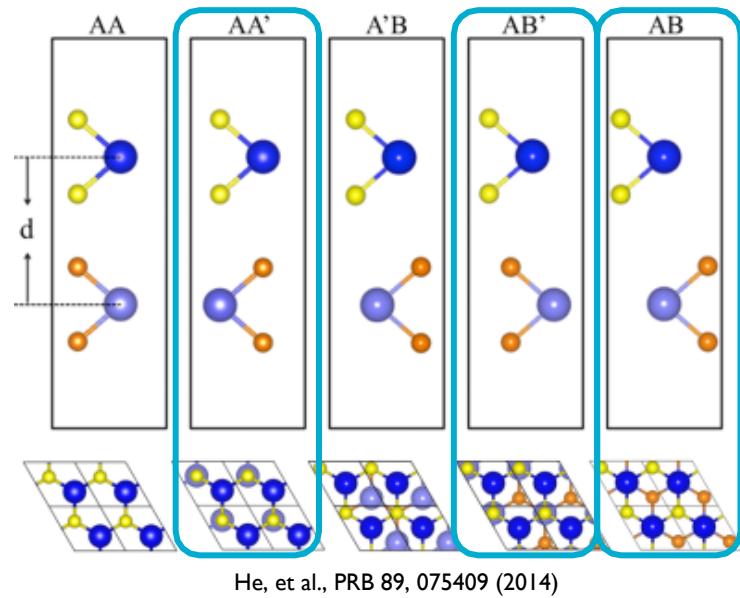
We found local variations of the Γ -point peak positions in multilayer WS_2



- The variations of the Γ -point peak position are 30-50meV
- Shape & size of the variations match the crystal grains in the Au-film
- The variations found in multilayer, but absent in single layer

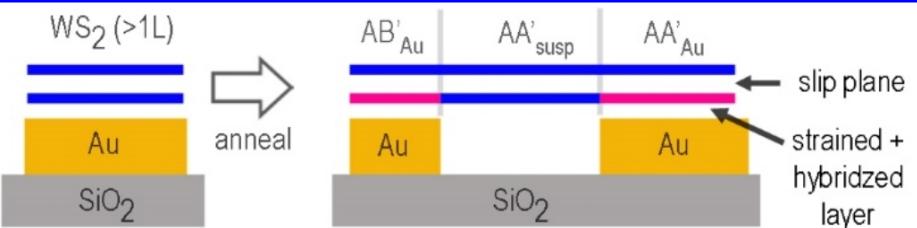
Hypothesis: layer slippage due to the strong adhesion between WS_2 & Au?

DFT modeling supports the layer slippage model



- Compared stacking sequences for 2L: AA', AB', and AB
 - AA' common for bulk WS₂
 - Alignment of one layer is slightly shifted with respect to another
- 20-50meV variations of Γ -point state depending on the stacking sequence
 - Similar to the PEEM result of 30-50meV variations
- Support the metal adhesion-induced layer slippage model resulting in the WS₂'s local electronic structure variations

Conclusion: electronic properties of TMD is
altered mechanically by the metal

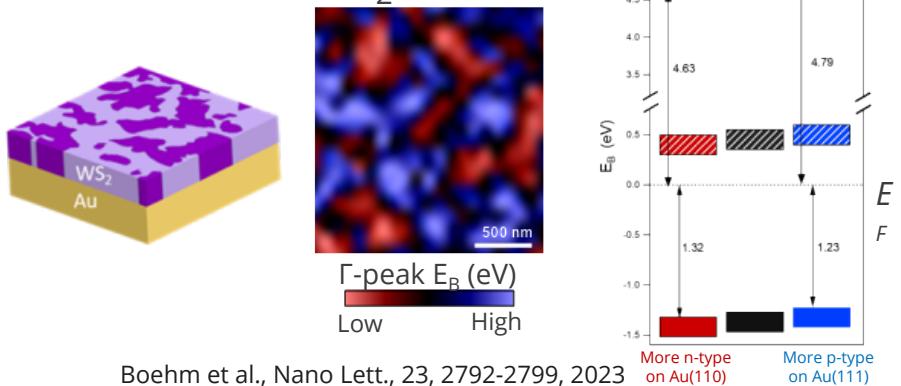


Take-home message:

- Microstructures of Au films plays important role in the electronic properties of the WS₂-Au contacts

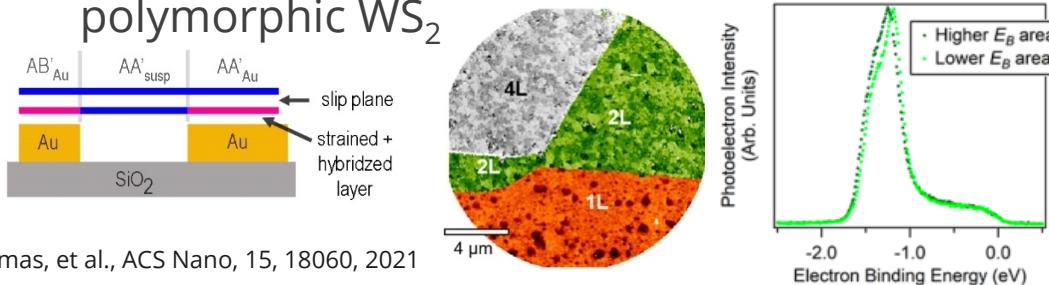
Concluding remarks

- Upside-down geometry allows direct access to semiconductor electronic properties & help us understand the metal contacts
- Microstructures of Au films plays important role at WS_2 -Au contacts
 - Au grains' facet govern the local electronic structures of WS_2



Boehm et al., Nano Lett., 23, 2792-2799, 2023

- Layer slippage induces stacking variation & polymorphic WS_2



Thomas, et al., ACS Nano, 15, 18060, 2021

Special thanks:

- WS_2 -Au interface interactions

N. Bartelt, C. Smyth, F. Leonard, C. J. Thomas, T.-M. Lu, R. G. Copeland, P. Mantos

Announcement:

Looking for postdoc candidate: investigating the optical resonances in TMD disk structures

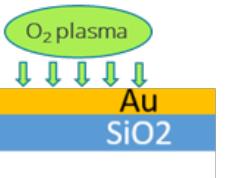
Thank you for your attention!



TMD on OPEN and Plasma-treated Au yield more uniform electronic structures



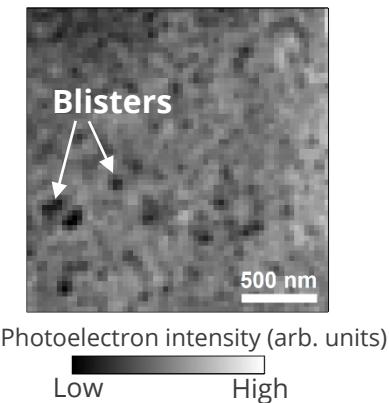
Pre-process



Exfoliation

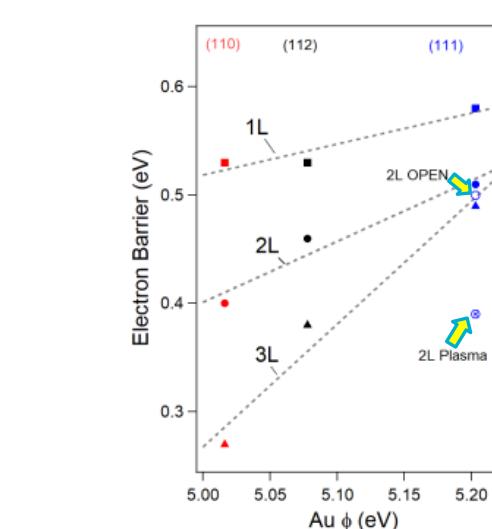
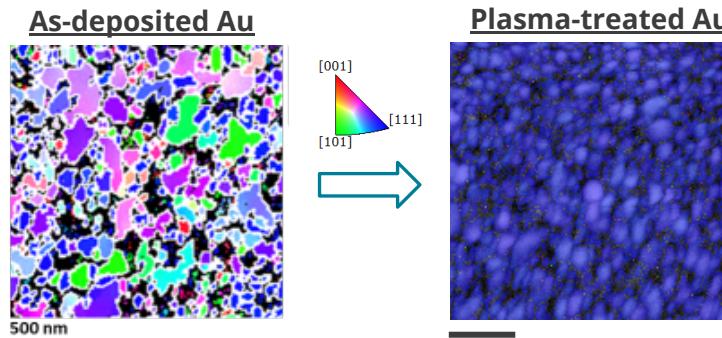
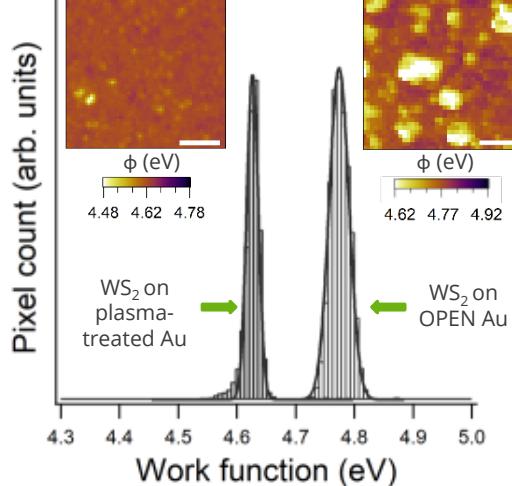


"Plasma-treated"



Photoelectron intensity (arb. units)

Low High



1 SBH for each
WS₂-Au junction

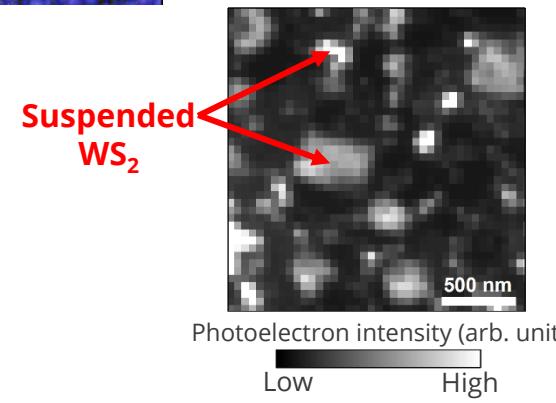
Post-process



Annealing

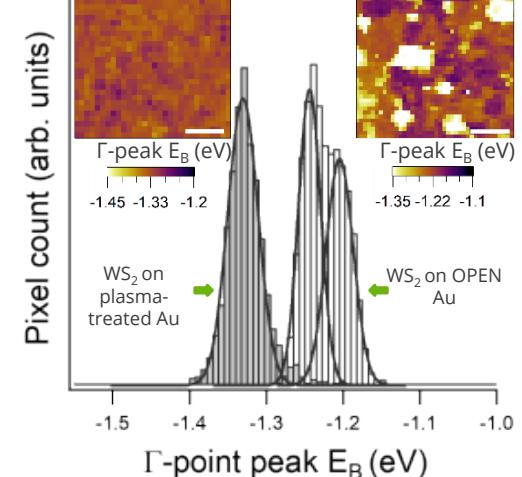


"OPEN"

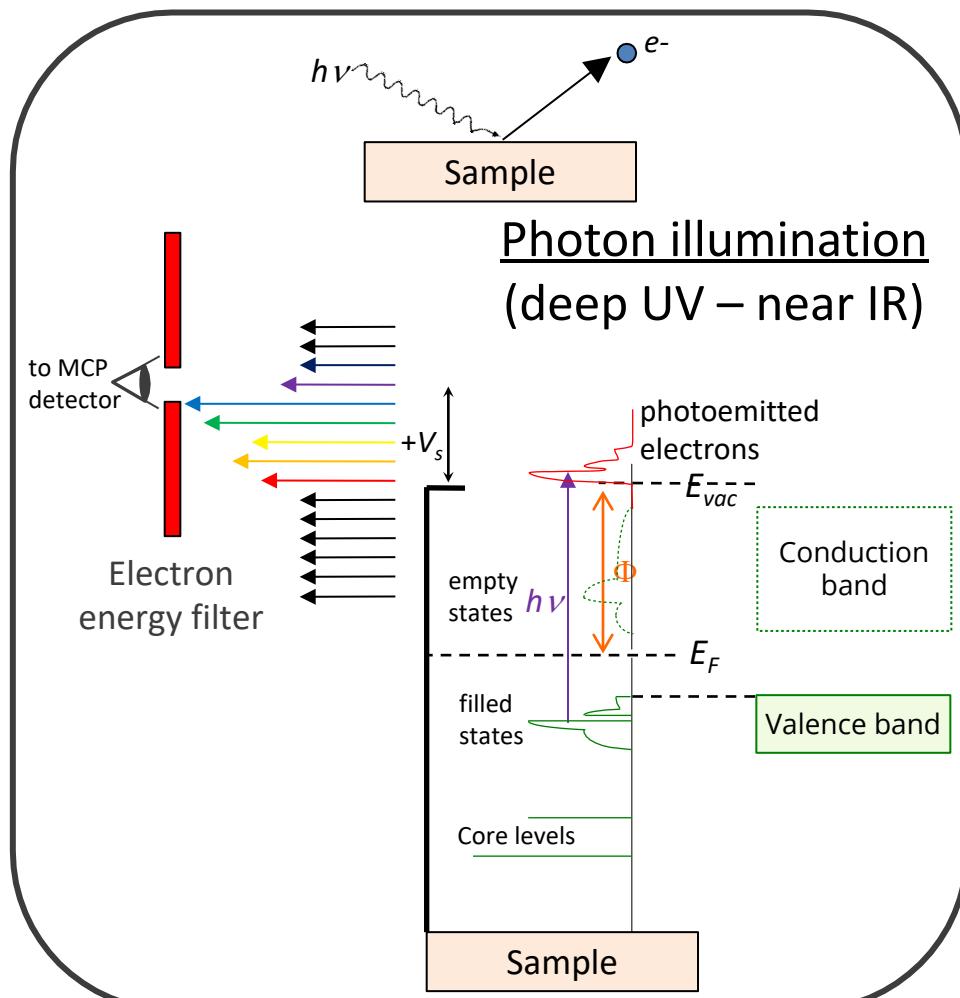


Photoelectron intensity (arb. units)

Low High



Reimagining what we can do with photoelectron imaging



Transition probability

Occupied electronic density of state

$$w_{i \rightarrow f} \propto \left| \left\langle f \left| H^{int} \right| i \right\rangle \right|^2 \delta(E_f - E_i - h\nu)$$

$$H^{int} = \frac{1}{2mc} (A \cdot p_{op} + p_{op} \cdot A)$$

Hamiltonian for the interaction

Vector potential of the electromagnetic radiation

Momentum operator of the electron

Electromagnetic field

Photoelectron yield varies strongly due to electromagnetic field distribution & occupied electron density of states

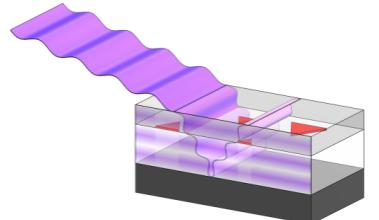
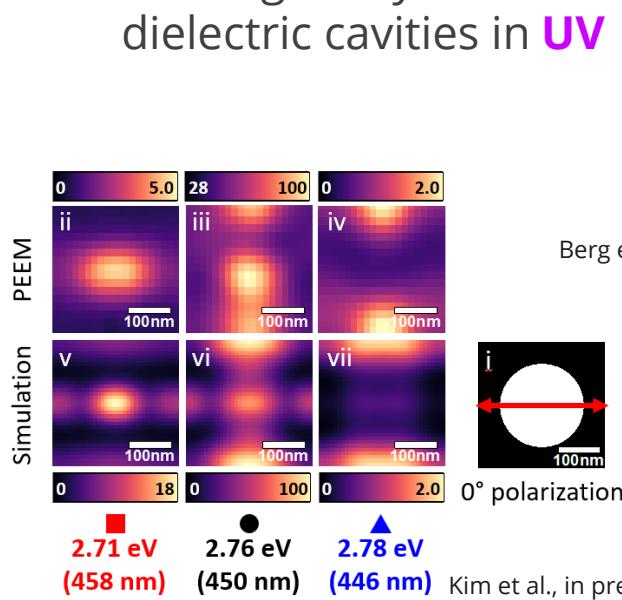
Light-matter interactions & electronic properties are probed based on the photoelectron intensity from the nanoscale materials

We examine electronic & optical properties using PEEM

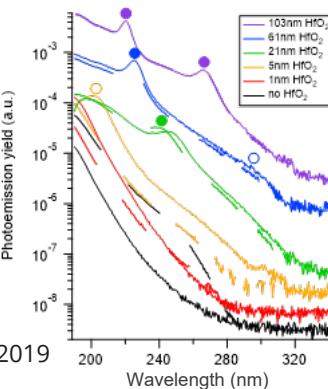


• Electromagnetic field imaging

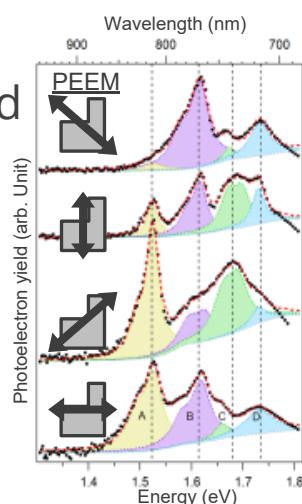
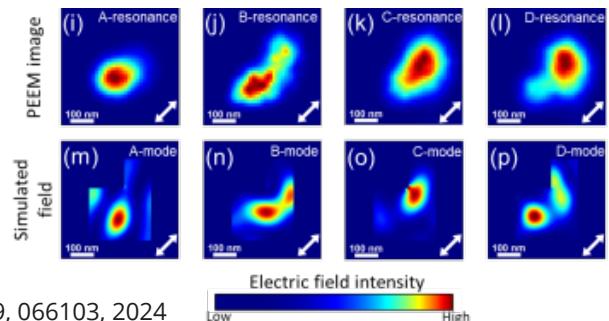
- Probing Fabry-Pérot resonance of dielectric cavities in **UV**



Berg et al., Phys. Rev. Applied, 12, 064064, 2019

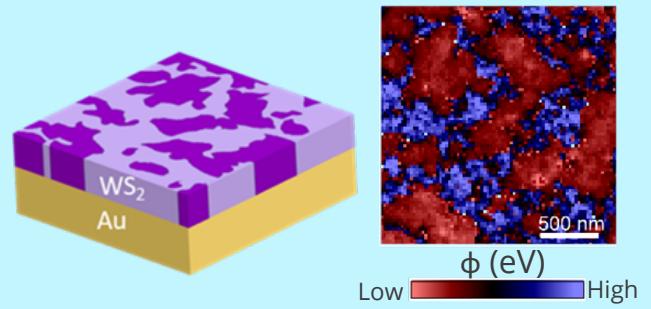


- Imaging **visible-near IR** resonances in Bound states in the continuum metasurfaces



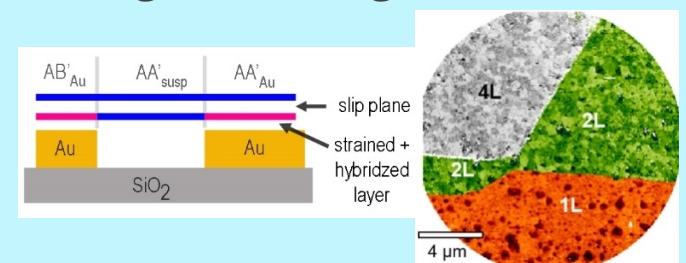
• Electronic structures of interfaces between WS₂ & gold

- Crystal facets of Au grains govern the local electronic structures of WS₂



Boehm et al., Nano Lett., 23, 2792-2799, 2023

- Strong interaction induced layer slippage between WS₂ & Au grains resulting in stacking variation



Thomas, et al., ACS Nano, 15, 18060, 2021